- 1. Consider an NMOS transistor with  $L_{eff}$ =25nm and  $V_{ds}$ =1V
  - (a) What is the electrical field (F) in  $V/\mu m$  in the channel between source and drain?

$$(F = V/L)$$

(b) With an electron mobility of  $\mu_n=500 \text{ cm}^2/(\text{V}\cdot\text{s})$ , what is the velocity of the electron in this field? (in m/s)?

(velocity 
$$v = \mu \times F$$
)

(c) At what  $V_{ds}$  voltage does the velocity reach  $10^5$  m/s?

2. How many capacitance values might we need to represent a 4-terminal transistor? (fourth terminal is body)

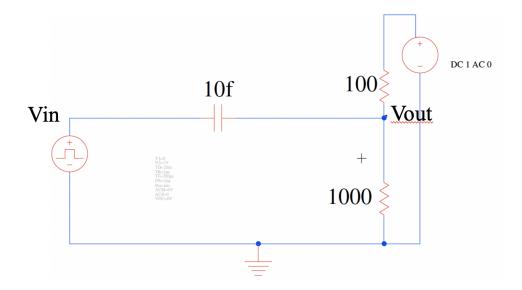


Hint: How many terminal pairs are there?

Terminal Pair	Capacitance

Use in class for notes to summarize cases and capacitances.

3. Assuming a step input from 0 to 1V by the pulse generator on the left, what does the voltage on Vout as a function of time look like?



**Hints:** What is the initial voltage? What is the steady-state voltage as  $t \to \infty$ ?